



**PATENT**  
Attorney Docket No. 401479

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:

Art Unit: 1742

IZUO et al.

Examiner: D. Valentine

Application No.: 10/009,521

Date of Allowability: November 21, 2003

Filed: December 11, 2001

Confirmation No.: 4369

For: METHOD AND APPARATUS  
FOR RADIATION ASSISTED  
ELECTROCHEMICAL ETCHING  
AND ETCHED PRODUCT

**RESPONSE TO NOTICE OF DRAWING INCONSISTENCY**

Mail Stop Issue Fee  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

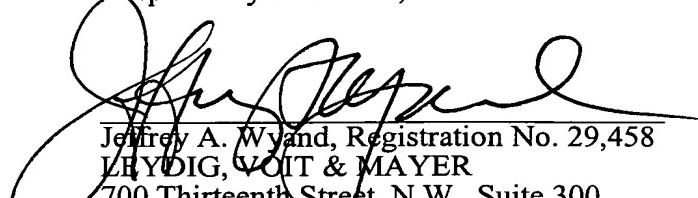
Dear Sir:

In response to the Notice of Drawing Inconsistency, Applicants request a specification amendment and a substitution of the attached replacement drawing sheet. The replacement drawing sheet is submitted to be consistent with the drawing amendment that accompanied the filing of the patent application and was part of a Preliminary Amendment. The specification was amended to conform to this drawing amendment but no replacement drawing sheet had been submitted because the Examiner indicated that the original drawings were satisfactory. The oversight in failing to submit the readily available drawing sheet is regretted.

The Notice made reference to Figure 2E but did not clearly indicate the issue. It is apparent that there is no Figure 2E in the patent application. Therefore, the incorrect brief description of the drawings at page 10 of the patent application is corrected in the accompanying specification amendment.

Entry of the replacement drawing sheet and of the specification amendment so that  
this patent application can be issued as a patent is respectfully requested.

Respectfully submitted,



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Date: May 12, 2004  
JAW:ves

**SPECIFICATION AMENDMENTS**

Replace the paragraph beginning at page 10, line 14 with:

Figs. 2A to ~~2E~~ 2D are drawings, each ~~of which~~ showing a cross sectional shape of a pore formed in the silicon substrate, ~~a~~ diameter of the pore, and ~~an~~ illumination in Experiment 2;